

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	((thin adj film adj transistor) and (conductive adj film) and (etch\$3 with (conductive adj film)) and (first with (insulating adj film)) and (second with film) and (second with electrode) and ((metal adj mask) with (vapor adj deposition)) and (film with organic)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/05 09:22
S1	2602	(TFT or (thin adj film adj transistor)) and electrode and insulat\$3 and (gate with (sidewall or (side adj wall) or (side adj surface)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/12 13:00
S2	2235	S1 and (insulat\$3 with substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 17:14
S3	1976	S2 and etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 17:14
S4	838	S3 and (TFT or (thin adj film adj transistor)).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 17:14
S5	230	S4 and side.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 21:49
S6	111	S5 and thin.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/04 09:27
S7	110	S6 and (gate with side)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 17:17
S8	93	S6 and (gate with side).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 17:26

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S9	11	S8 and (slant\$3 or slop\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 21:50
S10	2	S8 and asymmetric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 17:26
S11	9	("3493812" "4547789").PN. OR ("4924279").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/08 17:37
S12	12	("4547789").URPN.	USPAT	OR	ON	2005/12/08 17:45
S13	1544	438/149.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/04 09:38
S14	6	("4547789" "4924279" "4949141").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/12 13:00
S15	3133	(TFT or (thin adj film adj transistor)) and electrode and insulat\$3 and (gate with (sidewall or (side adj wall) or (side adj surface)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 21:49
S16	2722	S15 and (insulat\$3 with substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 21:49
S17	2413	S16 and etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 21:49
S18	992	S17 and (TFT or (thin adj film adj transistor)).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 21:49
S19	262	S18 and side.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 21:49

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S20	11	S19 and (slant\$3 or slop\$3) and organic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 21:50
S21	13	("4547789").URPN.	USPAT	OR	ON	2007/01/05 22:08
S22	1	S21 and organic	USPAT	OR	ON	2007/01/05 22:08
S23	6	(US-4924279-\$ or US-4949141-\$ or US-5574294-\$ or US-5010027-\$ or US-7138682-\$ or US-4547789-\$).did.	USPAT	OR	ON	2007/08/04 09:11
S24	3441	(TFT or (thin adj film adj transistor)) and electrode and insulat\$3 and (gate with (sidewall or (side adj wall) or (side adj surface)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/04 09:27
S25	3006	S24 and (insulat\$3 with substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/04 09:27
S26	2669	S25 and etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/04 09:27
S27	1081	S26 and (TFT or (thin adj film adj transistor)).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/04 09:27
S28	278	S27 and side.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/04 09:27
S29	36	S28 and thin.ti. and (metal with mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/04 09:34
S30	3	"6174819"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/04 09:34

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S31	2299	438/149.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/04 09:53
S32	1686	438/151.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/05 09:18